



Design Considerations for EM Pulse Fault Injection

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CARDIS 2019

What is EM-fault injection

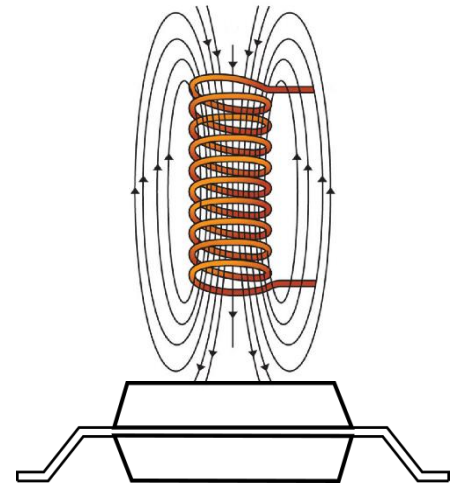
Injection of electromagnetic field into a target IC

Properties:

- + Locality → relatively good spatial resolution (100um - mm)
- + In theory no decapsulation needed → non invasive
- + Relatively good timing resolution
- + Can be done cheaply (100 euro)
- Completely black box behaviour of the device

Injected fields:

- E-field
- H-field
- Combination of both



H-field EM pulse injection

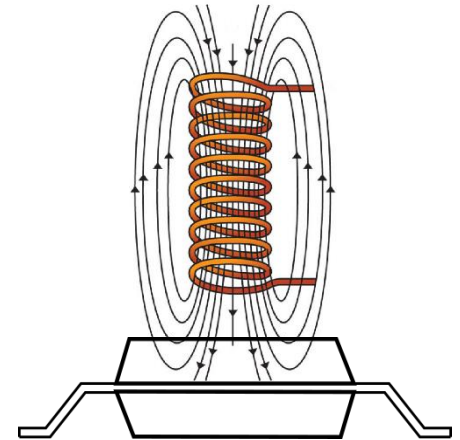
H-field probe characteristics:

- Solenoid shape
- Air or ferrite core
- 0.1- 10mm diameter
- 1 - 20 windings

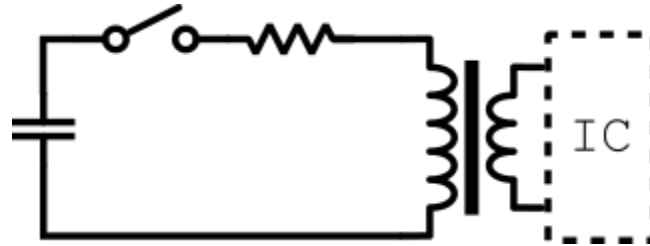
H-field EM pulse characteristics:

- ns rise times
- Currents in ampere range

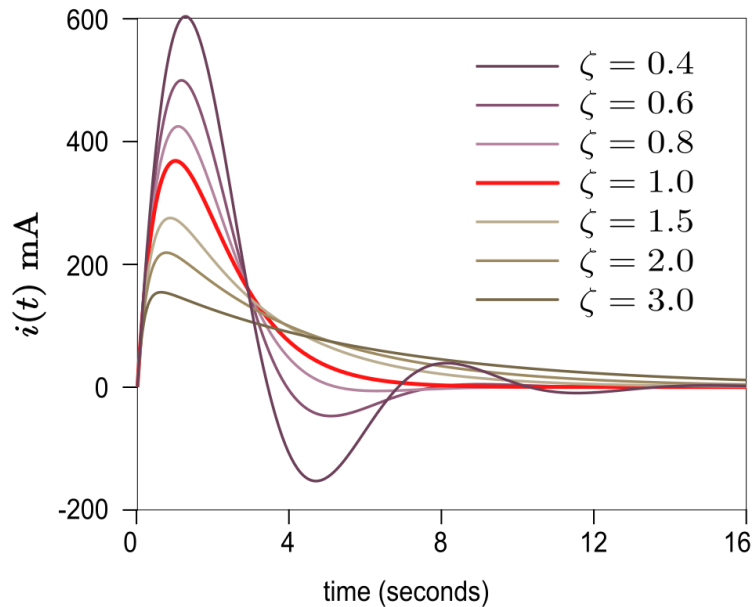
$$\text{Magnetic flux density : } B = \frac{k\mu_0 N}{2l} I \left[\frac{l}{\sqrt{l^2 + r^2}} \right]$$



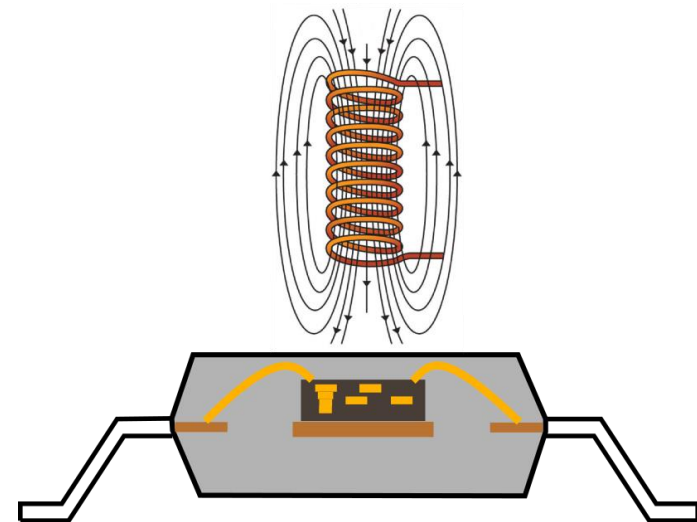
EM-pulse injection modelling



RLC response ($\zeta = \frac{R}{2} \sqrt{\frac{C}{L}}$)

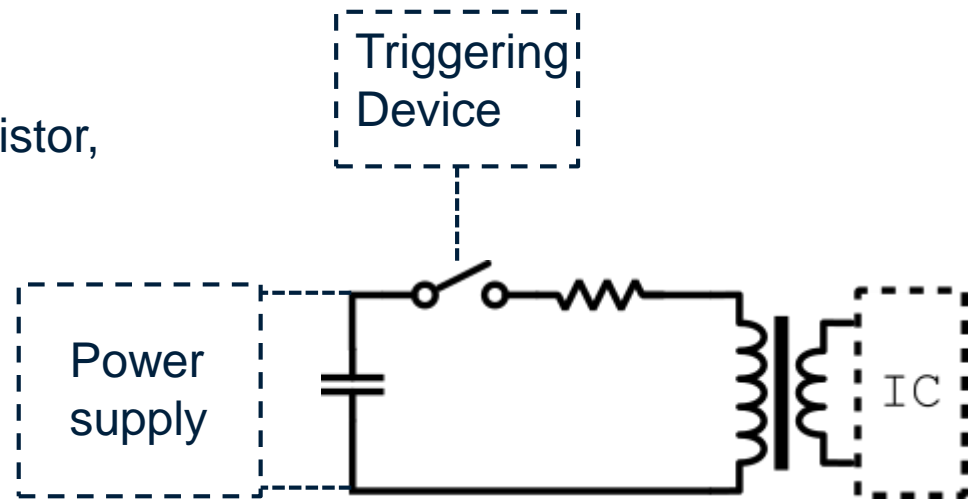


IC coupling



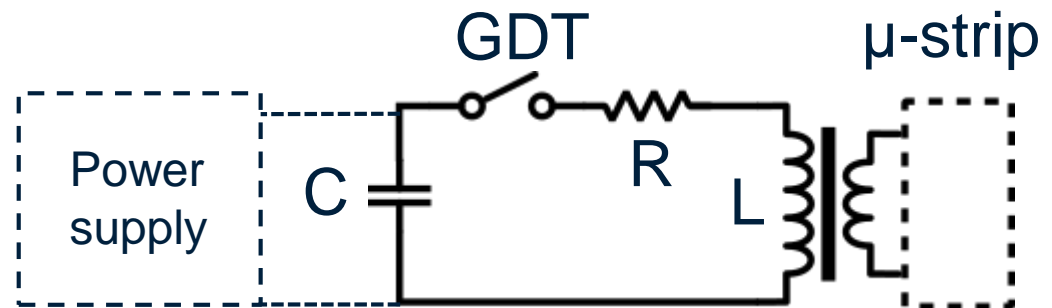
EM fault injection setup

- Switching element:
 - Fast rise time
 - Small parasitics
 - Consistent timing/ controllable
 - E.g Mosfet, IGBT, bipolar transistor, ...
- Triggering device:
 - High timing resolution
 - Small amount jitter
- Power supply
 - 100-500V DC
- Injection probe :
 - Characteristics are target dependent

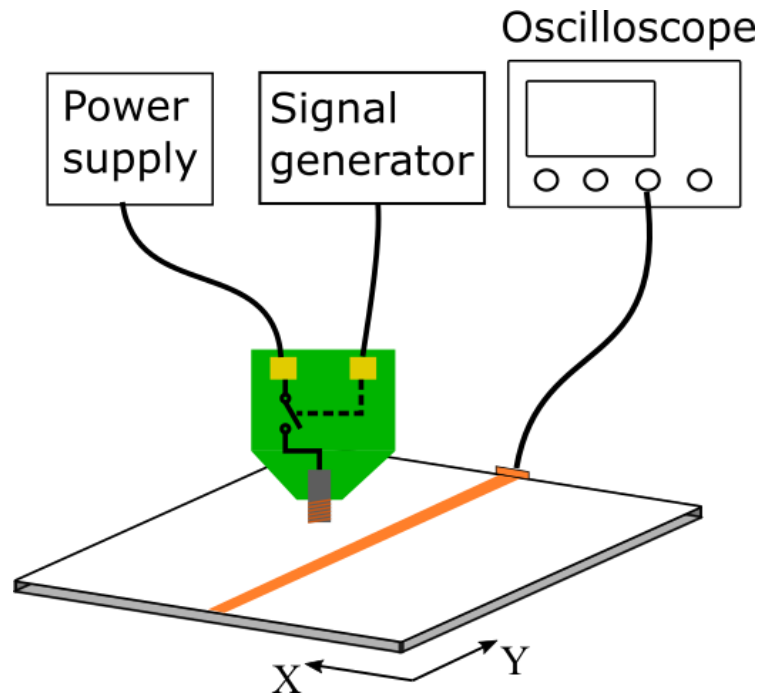


Characterization strategy

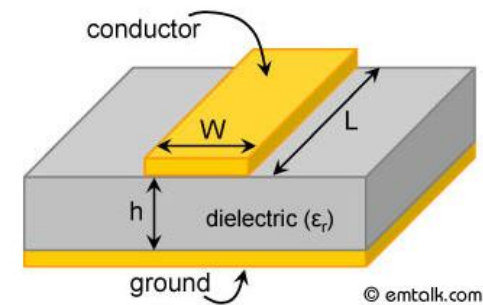
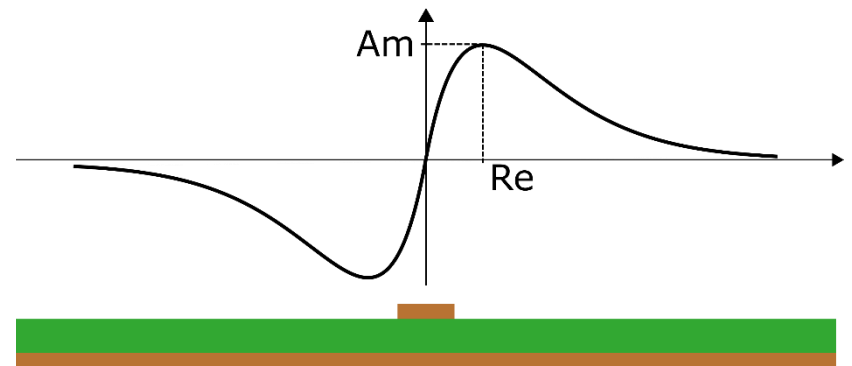
- Goal: illustrate how different passive components impact pulse response
- Test circuit:
 - Gas discharge tube switch (GDT) → 370V breakdown voltage
 - 47pF capacitor
 - 2mm ferrite core
 - 2 windings
- Test method:
 - 50Ω microstripline



Microstripline measurement method



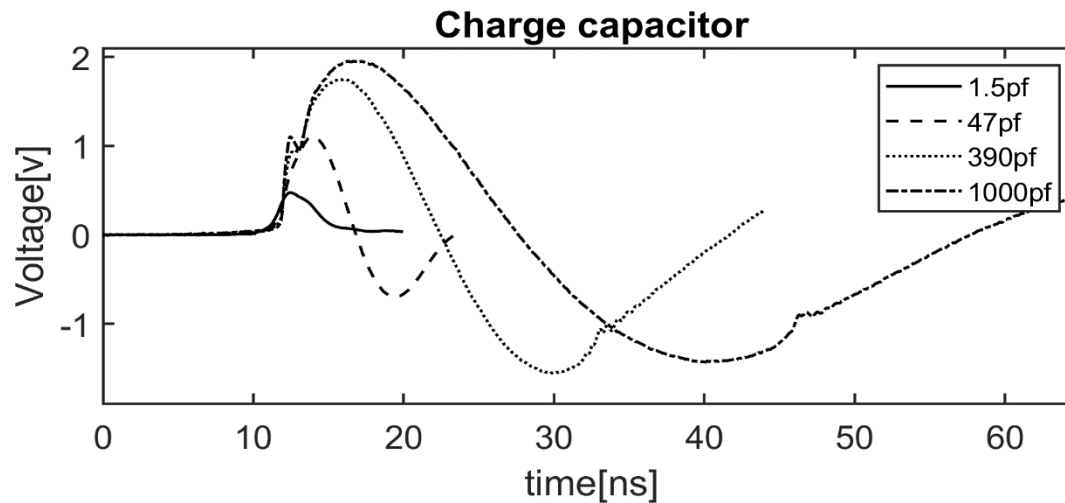
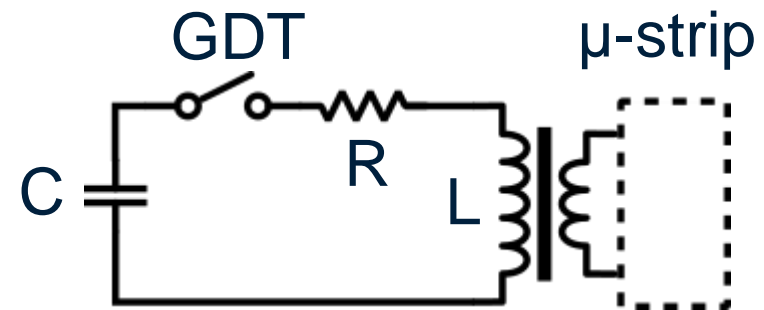
50Ω microstripline response



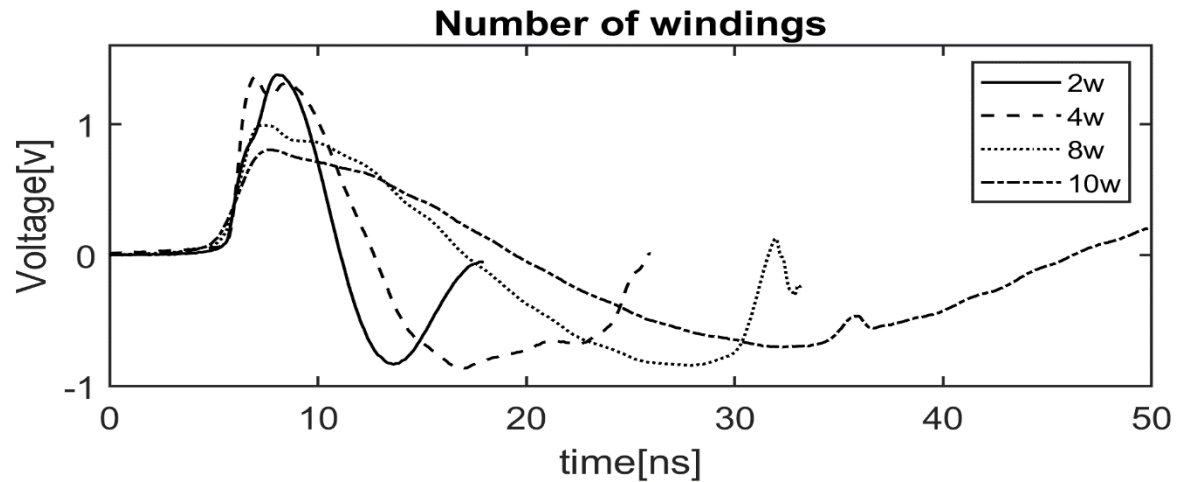
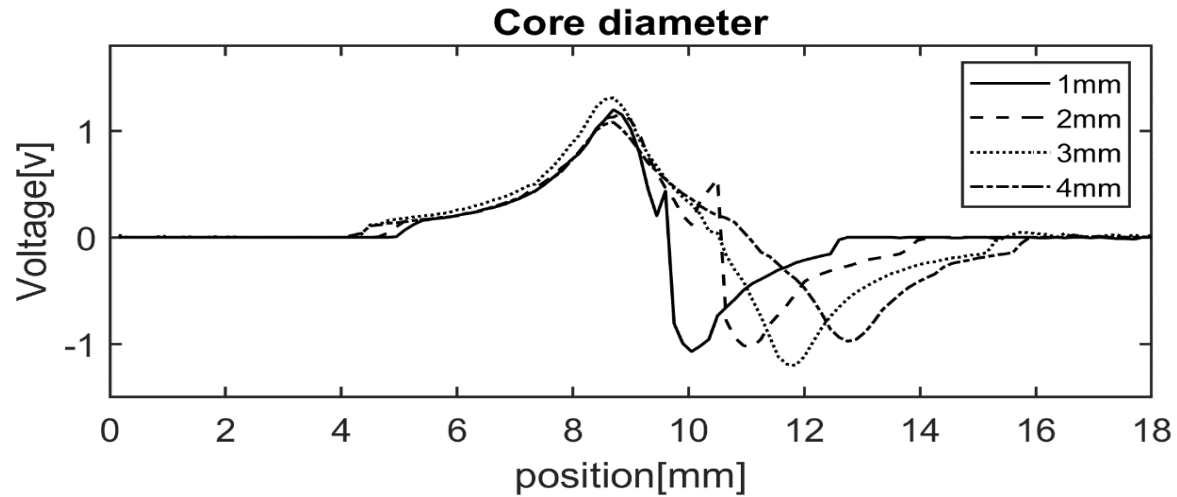
Probe characterization

➤ Parameters injection circuit:

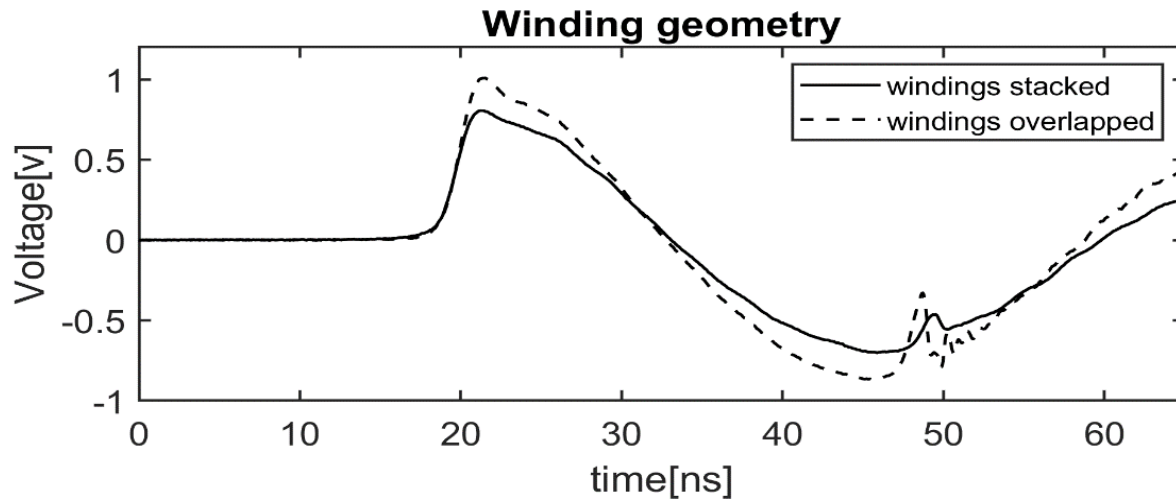
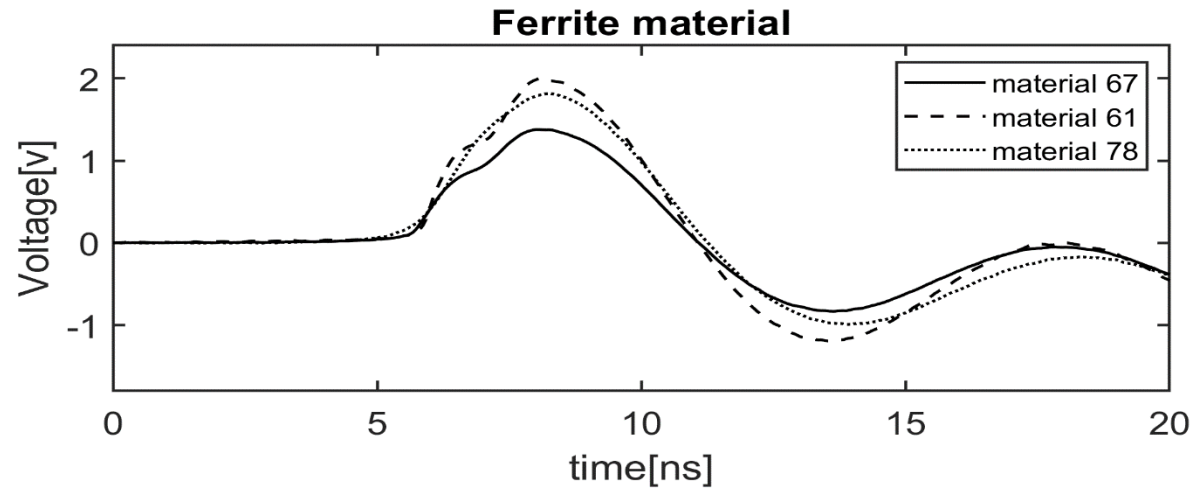
- Capacitance
- Ferrite core diameter
- Number of windings
- Ferrite type
- Winding geometry



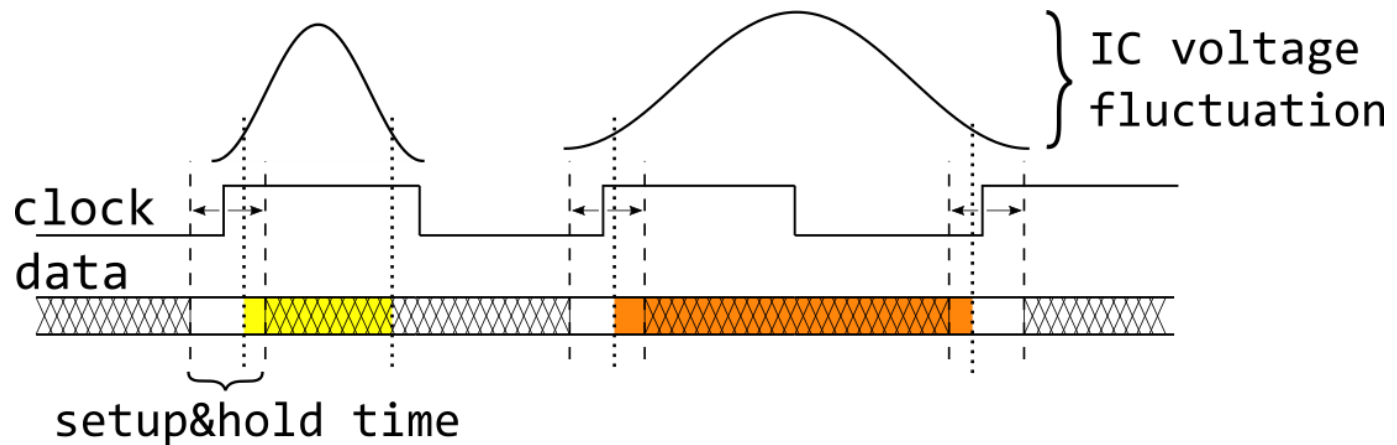
Probe characterization



Probe characterization



EM-pulse faulting mechanism



[1] Ordas et al., Evidence of a larger em-induced fault model. CARDIS 2015

Experimental validation

Goal:

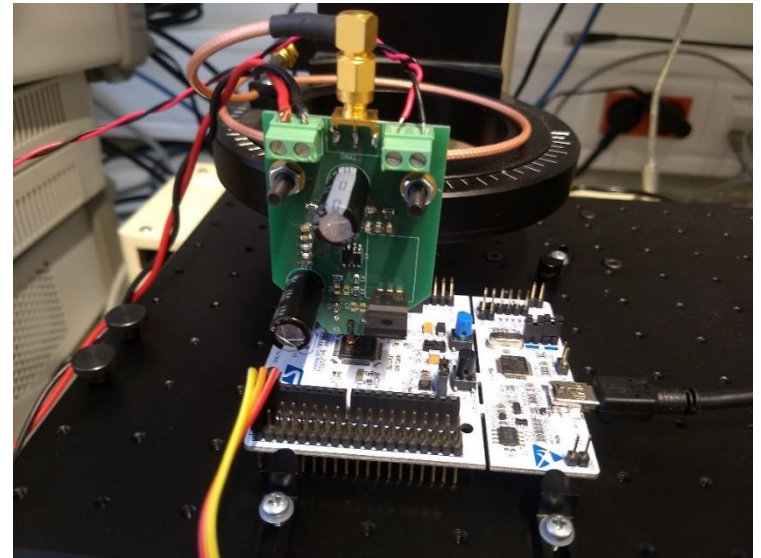
demonstrate the impact of the pulse shape on the fault pattern

Target device:

- STM32F411
- Clock frequency: 100MHz
- Not decapsulated

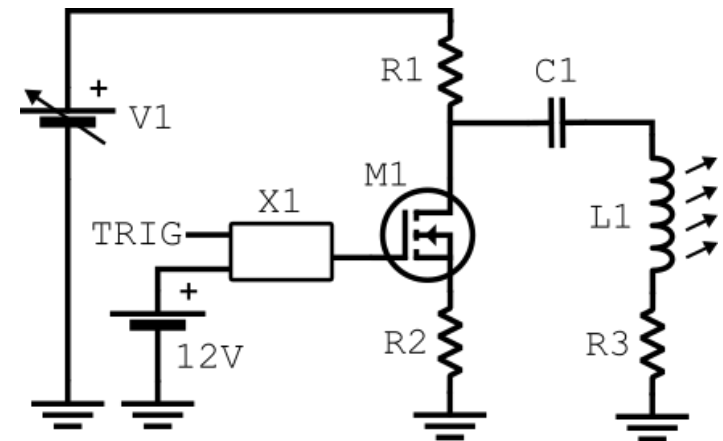
Target code:

- STM {r0-r9} (store multiple)
- Data: 0x55555555



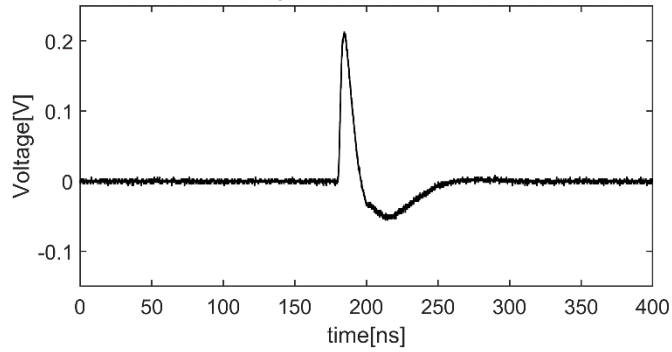
EM-fault injector

- Switching element:
 - MOSFET, n-channel
- Injection probe :
 - 0,75mm
 - 4 windings
- Triggering device:
 - Signal generator + Mosfet driver
- Power supply:
 - 100V - 600 V
- Passive components:
 - C1: 1000 pF
 - R2: 0.22 Ω
 - R3: 10 Ω

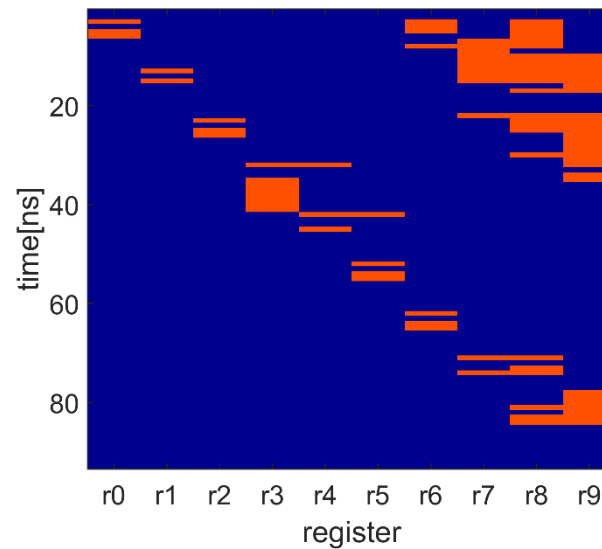
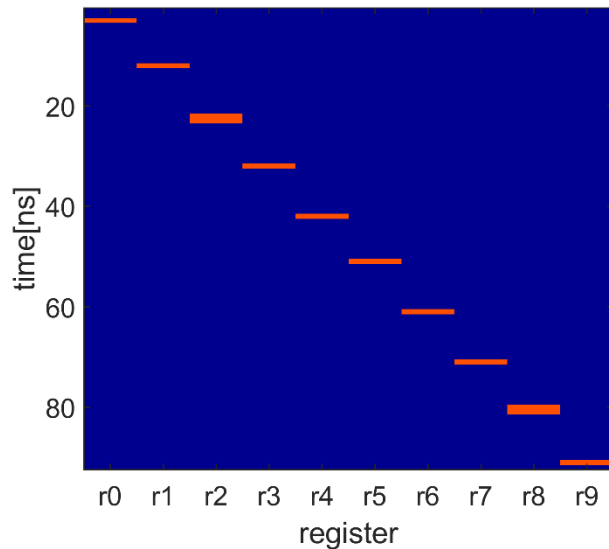
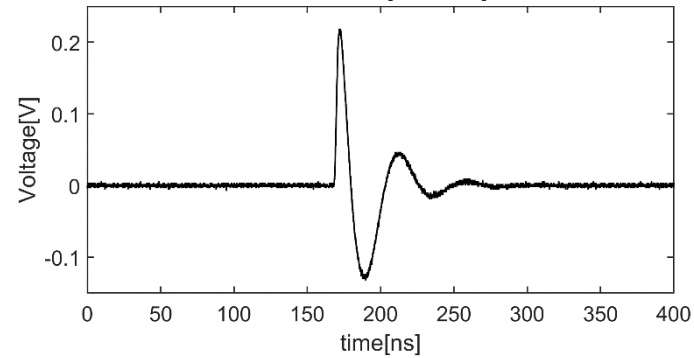


Experimental results

Critically damped probe



Under damped probe



Conclusion

- Illustrated the impact of the different components on the pulse shape
- Built an EM-pulse fault injection circuit based on the previous findings
- Demonstrated the effect different pulse shapes can have on a fault injection campaign